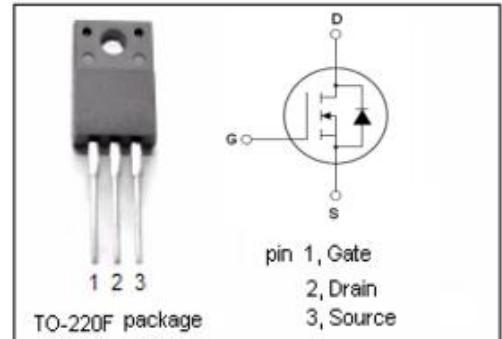


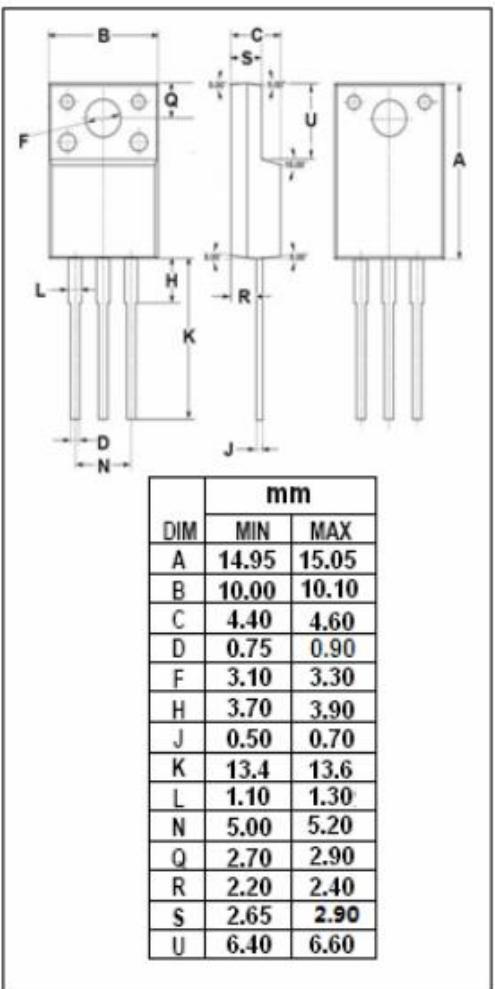
N-Channel MOSFET Transistor

FCPF1300N80Z FEATURES

- Drain-source R_{DS(on)} ≤ 1
- Fast Switching
- 100% avalanche tested
- Minimum Lot-Size: 1000



pin 1, Gate
2, Drain
3, Source



*

N-Channel MOSFET Transistor

FCPF1300N80Z

ELECTRICAL CHARACTERISTICS

T_c=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 1mA	800			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 250 μA	2.5		4.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =2A			1.3	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0V			±10	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =800V; V _{GS} = 0V			25	μA
		V _{DS} =640V; V _{GS} = 0V; T _c =125°C			250	
V _{SD}	Diode forward on voltage	I _{SD} =4A, V _{GS} = 0 V			1.2	V